Chang-Ju Lee

List of Publications by Year
in descending order

26 papers	187 citations	1307594 7 h-index	1058476 14 g-index
26 all docs	26 docs citations	26 times ranked	320 citing authors

#	Article	IF	Citations
1	Simultaneous Extraction of the Grain Size, Single-Crystalline Grain Sheet Resistance, and Grain Boundary Resistivity of Polycrystalline Monolayer Graphene. Nanomaterials, 2022, 12, 206.	4.1	2
2	Layer-resolved release of epitaxial layers in III-V heterostructure via a buffer-free mechanical separation technique. Science Advances, 2022, 8, eabl6406.	10.3	7
3	Evaluation of the average grain size of polycrystalline graphene using an electrical characterization method. Solid-State Electronics, 2021, 186, 108172.	1.4	1
4	Analytic model of spalling technique for thickness-controlled separation of single-crystalline semiconductor layers. Solid-State Electronics, 2020, 163, 107660.	1.4	8
5	Investigation of electrical characteristics of flexible CMOS devices fabricated with thickness-controlled spalling process. Solid-State Electronics, 2020, 173, 107901.	1.4	5
6	Effect of Graphene Doping Level near the Metal Contact Region on Electrical and Photoresponse Characteristics of Graphene Photodetector. Sensors, 2020, 20, 4661.	3.8	3
7	Extraction of intrinsic field-effect mobility of graphene considering effects of gate-bias-induced contact modulation. Journal of Applied Physics, 2020, 127, .	2.5	5
8	Effect of copper surface morphology on grain size uniformity of graphene grown by chemical vapor deposition. Current Applied Physics, 2019, 19, 1414-1420.	2.4	7
9	GaN-Based Ultraviolet Passive Pixel Sensor on Silicon (111) Substrate. Sensors, 2019, 19, 1051.	3.8	14
10	Multifunctional graphene sensor for detection of environment signals using a decoupling technique. Solid-State Electronics, 2019, 151, 40-46.	1.4	8
11	Optimized poly(methyl methacrylate)-mediated graphene-transfer process for fabrication of high-quality graphene layer. Nanotechnology, 2018, 29, 415303.	2.6	41
12	Selectively Enhanced UV-A Photoresponsivity of a GaN MSM UV Photodetector with a Step-Graded AlxGa1â^'xN Buffer Layer. Sensors, 2017, 17, 1684.	3.8	22
13	Graphene/Al₂O₃/AlGaN/GaN Schottky MISIM Diode for Sensing Double UV Bands. IEEE Sensors Journal, 2016, 16, 6903-6907.	4.7	6
14	Double-wavelength sensitive AlGaN/GaN MISIM UV sensor using multi-layer graphene as Schottky electrodes. , 2015, , .		0
15	GaN metalâ€“semiconductorâ€“metal UV sensor with multi-layer graphene as Schottky electrodes. Japanese Journal of Applied Physics, 2015, 54, 06FF08.	1.5	20
16	Hybrid UV Active Pixel Sensor Implemented Using GaN MSM UV Sensor and Si-Based Circuit. IEEE Sensors Journal, 2015, 15, 5071-5074.	4.7	11
17	Dual-wavelength sensitive AlGaN/GaN metal-insulator-semiconductor-insulator-metal ultraviolet sensor with balanced ultraviolet/visible rejection ratios. Applied Physics Letters, 2013, 103, .	3.3	17
18	High UV-visible rejection ratio of dual-wavelength detecting MISIM UV sensor with a thin Al<inf>2</inf>O<inf>3</inf> layer. , 2013, , .		0

#	Article	IF	Citations
19	Performance of GaN Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor with Regrown n+-Source/Drain on a Selectively Etched GaN. Japanese Journal of Applied Physics, 2013, 52, 061001.	1.5	4
20	Dual-band responsivity of AlGaN/GaN MSM UV photodiode. , 2012, , .		0
21	Enhanced UV-visible rejection ratio in an MSM UV photodetector fabricated on N-face GaN by thermal annealing effects. , 2012, , .		1
22	GaN schottky barrier MOSFET using transparent source/drain electrodes for UV-optoelectronic integration. Solid-State Electronics, 2012, 73, 78-80.	1.4	5
23	Vertical GaN schottky barrier diode on an N-face GaN layer formed by ELOG and laser-lift-off technique for high-power application. , 2011, , .		0
24	UV-A selective photo-responsivity in a GaN MSM photodetector using ITO schottky electrodes. , 2011, , .		0
25	Body bias effect of GaN schottky barrier MOSFET with ITO source/drain. , 2010, , .		0
26	GaN schottky barrier MOSFET using indium-tin-oxide as source, drain and gate material. , 2010, , .		0